

In the Specification

Page 5, Line 18, after "etch" please insert thereby serving as an etch stop layer for the subsequent etch.

In the Claims

Please amend claim 1 as set forth below.

1. (Amended) A method, comprising:

forming a contact hole through a first insulating layer that is self-aligned with respect to a transistor gate having a gate length less than 0.2 microns without forming a contact hole etch stop liner [layer].

Please amend claim 2 as set forth below.

2. (Amended) The method of claim 1, wherein:

forming [a] the contact hole includes reactive plasma etching through [a] the first insulating layer comprising non-densified doped silicon dioxide.

Please amend claim 3 as set forth below.

3. (Amended) The method of claim 1, wherein:

forming [a] the contact hole includes reactive plasma etching through [a] the first insulating layer comprising silicon dioxide having a concentration of phosphorous dopant that is greater than 5% by weight.